

Silicon NPN Power Transistors

2SD798

DESCRIPTION

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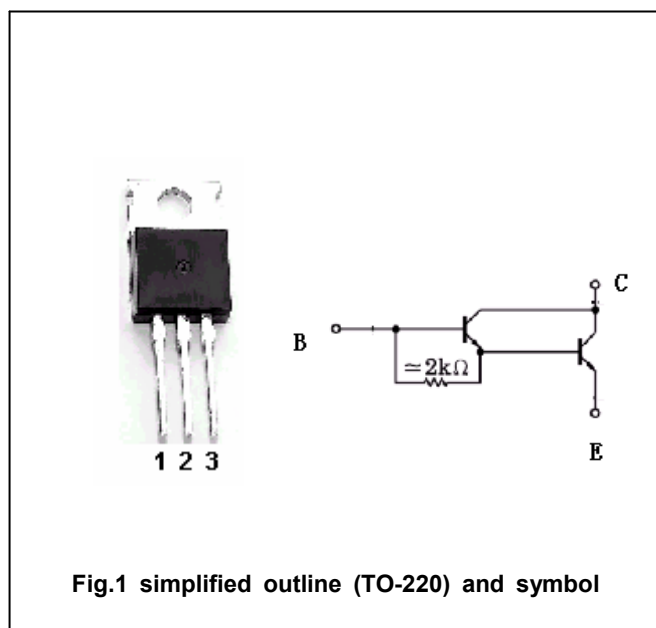
- With TO-220 package
- High voltage
- DARLINGTON

APPLICATIONS

- With switching and igniter applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V_{CBO}	Collector-base voltage	Open emitter	600	V
V_{CEO}	Collector-emitter voltage	Open base	300	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		6	A
I_B	Base current		1	A
P_C	Collector power dissipation	$T_C=25^\circ\text{C}$	30	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	$I_C=0.5A$; $L=40mH$	300			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=4A$; $I_B=0.04A$			2.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=4A$; $I_B=0.04A$			2.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=600V$; $I_E=0$			0.5	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=5V$; $I_C=0$			0.5	mA
h_{FE-1}	DC current gain	$I_C=2A$; $V_{CE}=2V$	1500			
h_{FE-2}	DC current gain	$I_C=4A$; $V_{CE}=2V$	200			
C_{OB}	Collector output capacitance	$f=1MHz$; $V_{CB}=50V$		35		pF

Switching times

t_{on}	Turn-on time	$I_{B1}=-I_{B2}=0.04A$ $V_{CC}\approx 100V$; $R_L=25\Omega$		1		μs
t_{stg}	Storage time			8		μs
t_f	Fall time			5		μs

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PACKAGE OUTLINE

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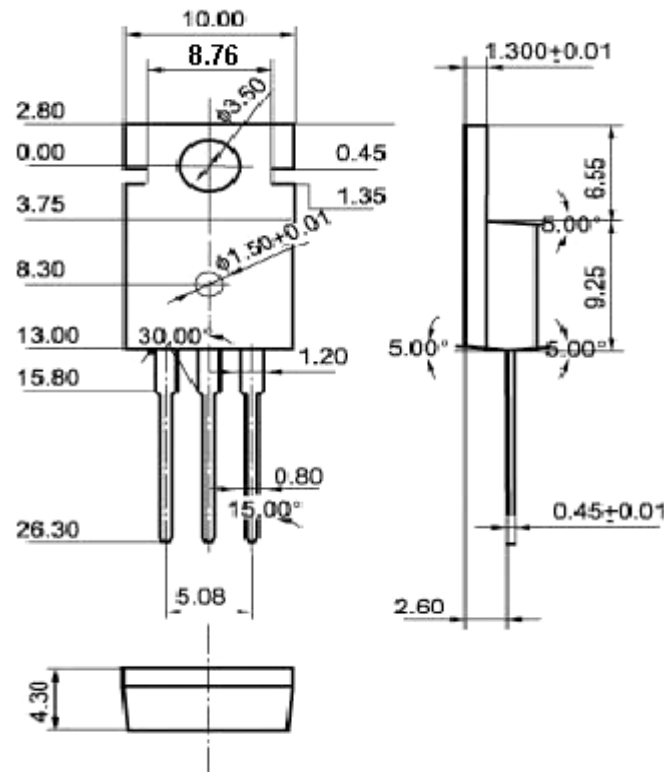


Fig.2 Outline dimensions